Abstracts

A New GaAs Power-MESFET with Large Unit Gate Width

K. Fricke, V. Krozer and H.L. Hartnagel. "A New GaAs Power-MESFET with Large Unit Gate Width." 1989 MTT-S International Microwave Symposium Digest 89.1 (1989 Vol. I [MWSYM]): 389-392.

A new GaAs-power-FET is proposed which uses an additional transmission line feeder parallel to the gate. With a suitable termination at the end of this transmission line and a unit gate width of 2mm the fabricated device shows excellent power handling capabilities and an increased output resistance at 4 GHz. It is demonstrated that this approach leads to higher output power and easier matching of GaAs-power-FET.

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